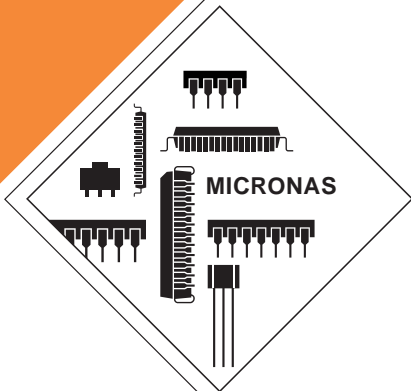


DATA SHEET

HAL700, HAL740 Hall-Effect Sensors with Independent Outputs



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Dual Hall-Effect Sensors with Independent Outputs

1. Introduction

The HAL700 and the HAL740 are monolithic CMOS Hall-effect sensors consisting of two independent switches controlling two independent open-drain outputs. The Hall plates of the two switches are spaced 2.35 mm apart.

The devices include temperature compensation and active offset compensation. These features provide excellent stability and matching of the switching points in the presence of mechanical stress over the whole temperature and supply voltage range.

The sensors are designed for industrial and automotive applications and operate with supply voltages from 3.8 V to 24 V in the ambient temperature range from -40 °C up to 125 °C.

The HAL700 and the HAL740 are available in the SMD package SOT-89B.

1.1. Features

- two independent Hall-switches
- distance of Hall plates: 2.35 mm
- switching offset compensation at typically 150 kHz
- operation from 3.8 V to 24 V supply voltage
- operation with static and dynamic magnetic fields up to 10 kHz
- overvoltage protection at all pins
- reverse-voltage protection at V_{DD} -pin
- robustness of magnetic characteristics against mechanical stress
- short-circuit protected open-drain outputs by thermal shut down
- constant switching points over a wide supply voltage range
- EMC corresponding to DIN 40839

1.2. Family Overview

The types differ according to the switching behavior of the magnetic switching points at the both Hall plates S1 and S2.

Type	Switching Behavior	See Page
HAL700	S1: latching S2: latching	14
HAL740	S1: unipolar north sensitive S2: unipolar south sensitive	16

Latching Sensors:

The output turns low with the magnetic south pole on the branded side of the package. The output maintains its previous state if the magnetic field is removed. For changing the output state, the opposite magnetic field polarity must be applied.

Unipolar Sensors:

In case of a south-sensitive switch, the output turns low with the magnetic south pole on the branded side of the package and turns high if the magnetic field is removed. The switch does not respond to the magnetic north pole on the branded side.

In case of a north-sensitive switch, the output turns low with the magnetic north pole on the branded side of the package and turns high if the magnetic field is removed. The switch does not respond to the magnetic south pole on the branded side.

1.3. Marking Code

All Hall sensors have a marking on the package surface (branded side). This marking includes the name of the sensor and the temperature range.

Type	Temperature Range	
	K	E
HAL700	700K	700E
HAL740	740K	740E

1.3.1. Special Marking of Prototype Parts

Prototype parts are coded with an underscore beneath the temperature range letter on each IC. They may be used for lab experiments and design-ins but are not intended to be used for qualification tests or as production parts.

1.4. Operating Junction Temperature Range

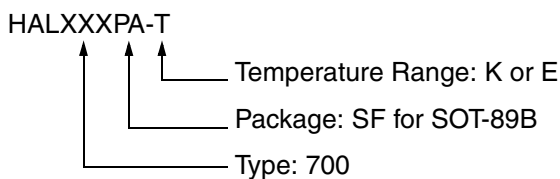
The Hall sensors from Micronas are specified to the chip temperature (junction temperature T_J).

K: $T_J = -40\text{ °C to }+140\text{ °C}$

E: $T_J = -40\text{ °C to }+100\text{ °C}$

The relationship between ambient temperature (T_A) and junction temperature is explained in Section 5.1. on page 18.

1.5. Hall Sensor Package Codes



Example: **HAL700SF-K**

- Type: 700
- Package: SOT-89B
- Temperature Range: $T_J = -40\text{ °C to }+140\text{ °C}$

Hall sensors are available in a wide variety of packaging quantities. For more detailed information, please refer to the brochure: "Hall Sensors: Ordering Codes, Packaging, Handling".

1.6. Solderability

All packages: according to IEC68-2-58

During soldering, reflow processing and manual reworking, a component body temperature of 260 °C should not be exceeded.

Components stored in the original packaging should provide a shelf life of at least 12 months, starting from the date code printed on the labels, even in environments as extreme as 40 °C and 90% relative humidity.

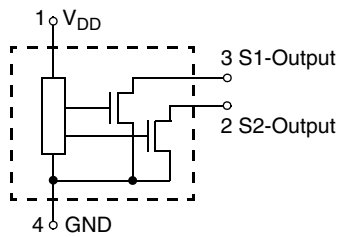


Fig. 1-1: Pin configuration

2. Functional Description

The HAL700 and the HAL740 are monolithic integrated circuits with two independent subblocks each consisting of a Hall plate and the corresponding comparator. Each subblock independently switches the comparator output in response to the magnetic field at the location of the corresponding sensitive area. If a magnetic field with flux lines perpendicular to the sensitive area is present, the biased Hall plate generates a Hall voltage proportional to this field. The Hall voltage is compared with the actual threshold level in the comparator. The subblocks are designed to have closely matched switching points. The output of comparator 1 attached to S1 controls the open drain output at Pin 3. Pin 2 is set according to the state of comparator 2 connected to S2.

The temperature-dependent bias – common to both subblocks – increases the supply voltage of the Hall plates and adjusts the switching points to the decreasing induction of magnets at higher temperatures. If the magnetic field exceeds the threshold levels, the comparator switches to the appropriate state. The built-in hysteresis prevents oscillations of the outputs.

The magnetic offset caused by mechanical stress is compensated for by use of “switching offset compensation techniques”. Therefore, an internal oscillator provides a two-phase clock to both subblocks. For each subblock, the Hall voltage is sampled at the end of the first phase. At the end of the second phase, both sampled and actual Hall voltages are averaged and compared with the actual switching point.

Shunt protection devices clamp voltage peaks at the output pins and V_{DD} -pin together with external series resistors. Reverse current is limited at the V_{DD} -pin by an internal series resistor up to -15 V . No external reverse protection diode is needed at the V_{DD} -pin for reverse voltages ranging from 0 V to -15 V .

Fig. 2–2 and Fig. 2–3 on page 6 show how the output signals are generated by the HAL700 and the HAL740. The magnetic flux density at the locations of the two Hall plates is shown by the two sinusoidal curves at the top of each diagram. The magnetic switching points are depicted as dashed lines for each Hall plate separately.

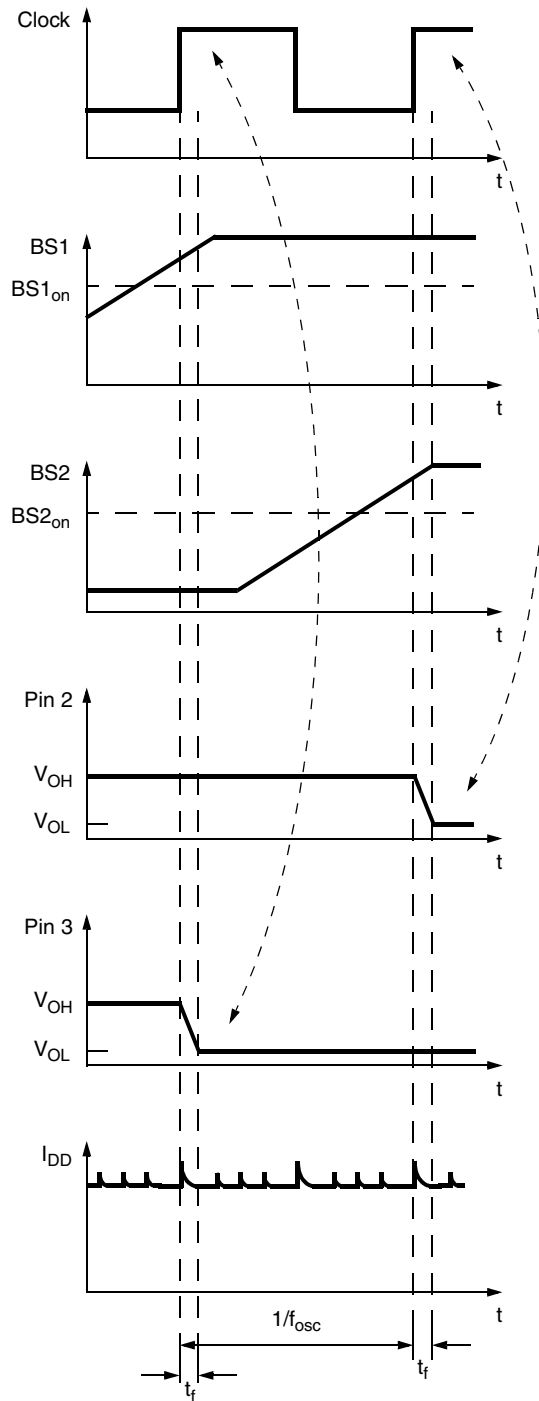


Fig. 2–1: HAL700 timing diagram with respect to the clock phase

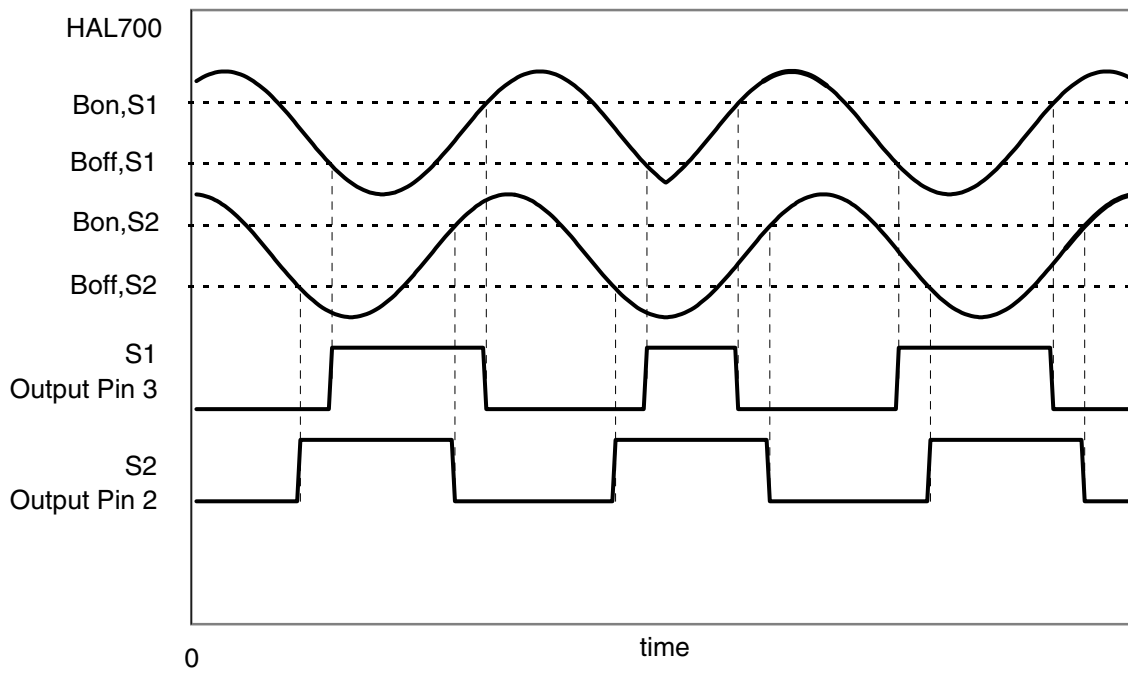


Fig. 2-2: HAL 700 timing diagram

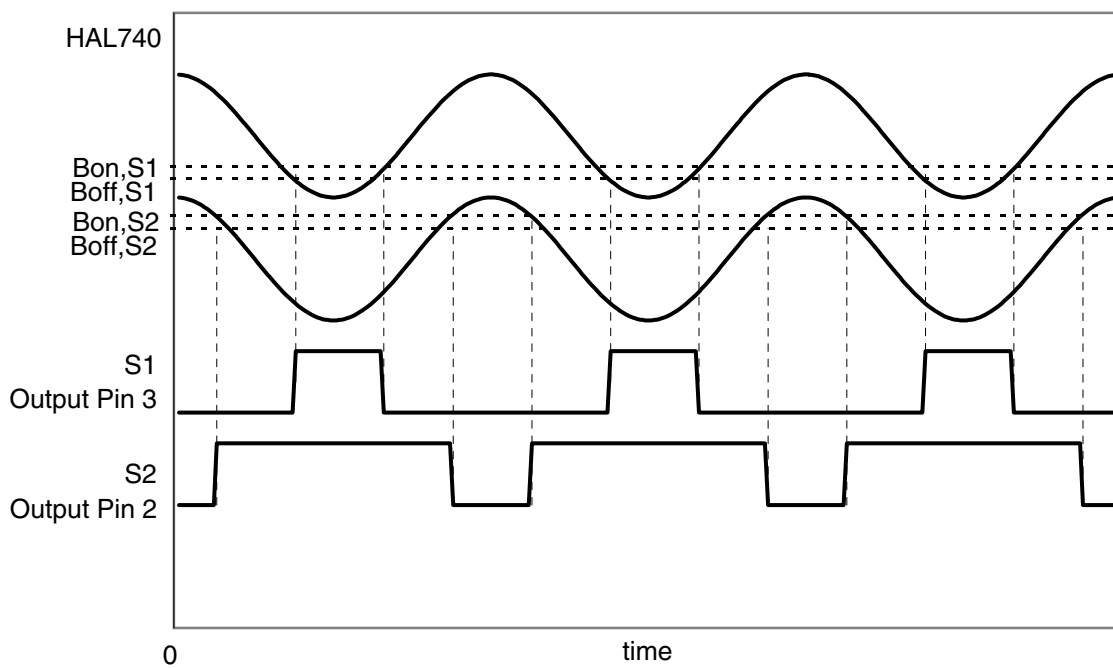


Fig. 2-3: HAL 740 timing diagram

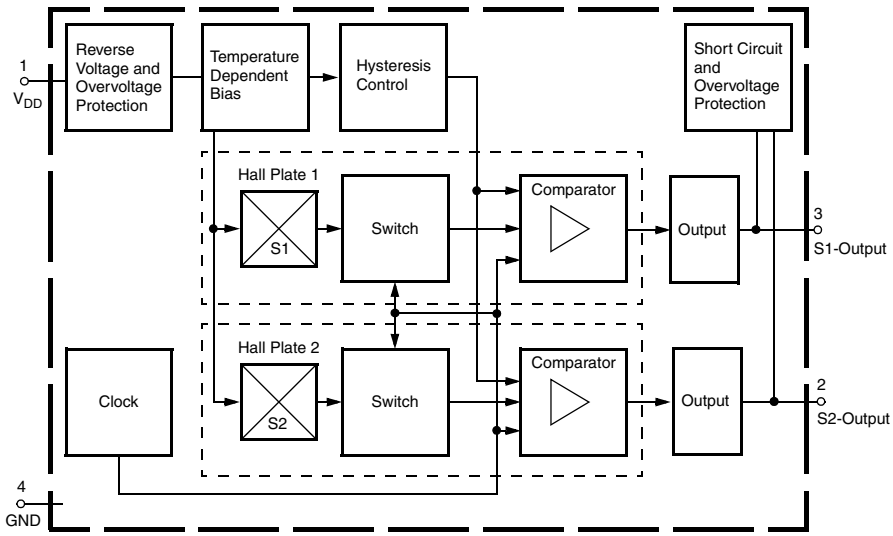
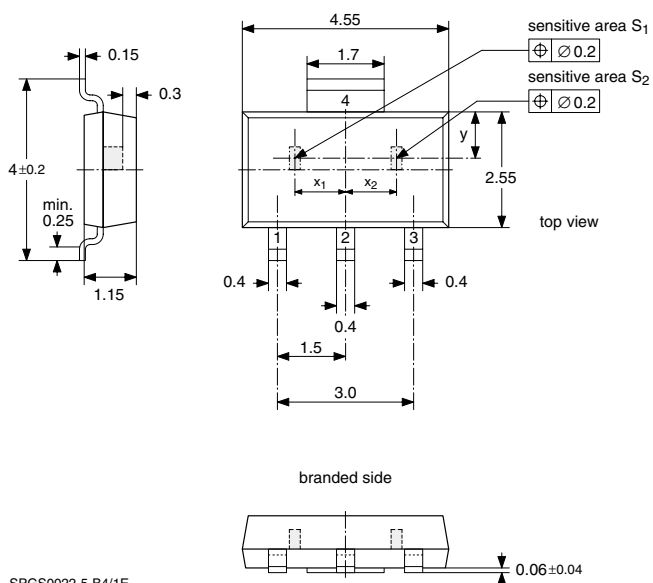


Fig. 2-4: HAL 700 and HAL 740 block diagram

3. Specifications

3.1. Outline Dimensions



SPGS0022-5-B4/1E

Fig. 3-1:
 Plastic Small Outline Transistor Package
(SOT-89B)
 Weight approximately 0.035 g
 Dimensions in mm

3.2. Dimensions of Sensitive Areas

Dimensions: 0.25 mm × 0.12 mm

3.3. Positions of Sensitive Areas

	SOT-89B
x_1+x_2	(2.35 ± 0.001) mm
$x_1=x_2$	1.175 mm nominal
y	0.975 mm nominal

Note: For all package diagrams, a mechanical tolerance of ± 0.05 mm applies to all dimensions where no tolerance is explicitly given.

3.4. Absolute Maximum Ratings

Symbol	Parameter	Pin No.	Min.	Max.	Unit
V _{DD}	Supply Voltage	1	-15	28 ¹⁾	V
V _O	Output Voltage	2, 3	-0.3	28 ¹⁾	V
I _O	Continuous Output Current	2, 3	-	20 ¹⁾	mA
T _J	Junction Temperature Range		-40	170	°C
1) as long as T _{Jmax} is not exceeded					

Stresses beyond those listed in the “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only. Functional operation of the device at these or any other conditions beyond those indicated in the “Recommended Operating Conditions/Characteristics” of this specification is not implied. Exposure to absolute maximum ratings conditions for extended periods may affect device reliability.

3.4.1. Storage, Moisture Sensitivity Class, and Shelf Life

Storage has no influence on the electrical and magnetic characteristics of the sensors. However, under disadvantageous conditions, extended storage time can lead to alteration of the lead plating, which affects the soldering process.

Moisture Sensitivity Class:

The package SOT-89B achieves level 1 according to J-STD-020A “Moisture/Reflow Sensitivity Classification for Non-hermetic Solid State Surface Mount Devices”. If the sensors are stored at maximum 30 °C and maximum 90% relative humidity no Dry Pack is required.

The permissible storage time (shelf life) of the sensors would be minimum 12 month, beginning from the date of manufacturing, if they are stored in the original packaging at maximum 40 °C ambient temperature and maximum 90% relative humidity.

3.5. Recommended Operating Conditions

Symbol	Parameter	Pin No.	Min.	Typ.	Max.	Unit
V _{DD}	Supply Voltage	1	3.8	-	24	V
I _O	Continuous Output Current	3	0	-	10	mA
V _O	Output Voltage (output switch off)	3	0	-	24	V

3.6. Electrical Characteristics

at $T_J = -40\text{ }^\circ\text{C}$ to $+140\text{ }^\circ\text{C}$, $V_{DD} = 3.8\text{ V}$ to 24 V , as not otherwise specified in Test Conditions.

Typical characteristics for $T_J = 25\text{ }^\circ\text{C}$ and $V_{DD} = 5\text{ V}$.

Symbol	Parameter	Pin No.	Min.	Typ.	Max.	Unit	Test Conditions
I_{DD}	Supply Current	1	3	5.5	9	mA	$T_J = 25\text{ }^\circ\text{C}$
I_{DD}	Supply Current over Temperature Range	1	2	7	10	mA	
V_{DDZ}	Overshoot Protection at Supply	1	–	28.5	32	V	$I_{DD} = 25\text{ mA}$, $T_J = 25\text{ }^\circ\text{C}$, $t = 2\text{ ms}$
V_{OZ}	Overshoot Protection at Output	2, 3	–	28	32	V	$I_O = 20\text{ mA}$, $T_J = 25\text{ }^\circ\text{C}$, $t = 15\text{ ms}$
V_{OL}	Output Voltage	2, 3	–	130	280	mV	$I_{OL} = 10\text{ mA}$, $T_J = 25\text{ }^\circ\text{C}$
V_{OL}	Output Voltage over Temperature Range	2, 3	–	130	400	mV	$I_{OL} = 10\text{ mA}$
I_{OH}	Output Leakage Current	2, 3	–	0.06	0.1	μA	Output switched off, $T_J = 25\text{ }^\circ\text{C}$, $V_{OH} = 3.8\text{ V}$ to 24 V
I_{OH}	Output Leakage Current over Temperature Range	2, 3	–	–	10	μA	Output switched off, $T_J \leq 140\text{ }^\circ\text{C}$, $V_{OH} = 3.8\text{ V}$ to 24 V
f_{osc}	Internal Sampling Frequency over Temperature Range	–	100	150	–	kHz	
$t_{en(O)}$	Enable Time of Output after Setting of V_{DD}	1	–	50	–	μs	$V_{DD} = 12\text{ V}$, $B > B_{on} + 2\text{ mT}$ or $B < B_{off} - 2\text{ mT}$
t_r	Output Rise Time	2, 3	–	0.2	–	μs	$V_{DD} = 12\text{ V}$, $R_L = 2.4\text{ k}\Omega$, $C_L = 20\text{ pF}$
t_f	Output FallTime	2, 3	–	0.2	–	μs	$V_{DD} = 12\text{ V}$, $R_L = 2.4\text{ k}\Omega$, $C_L = 20\text{ pF}$
R_{thSB} SOT-89B	Thermal Resistance Junction to Substrate Backside	–	–	150	200	K/W	Fiberglass Substrate 30 mm x 10mm x 1.5mm, pad size see Fig. 3–2

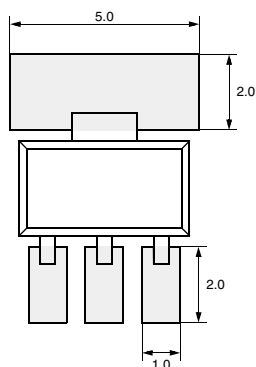
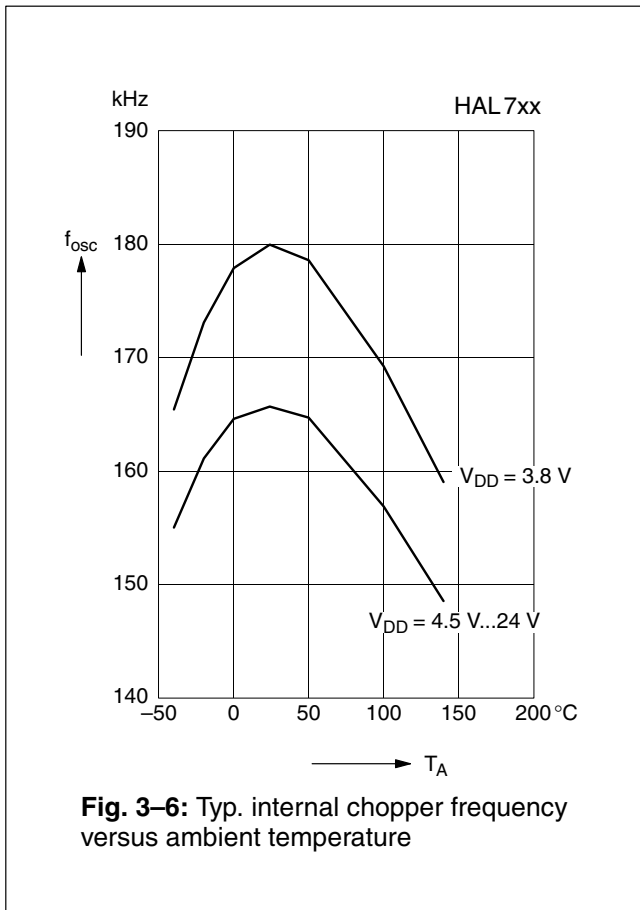
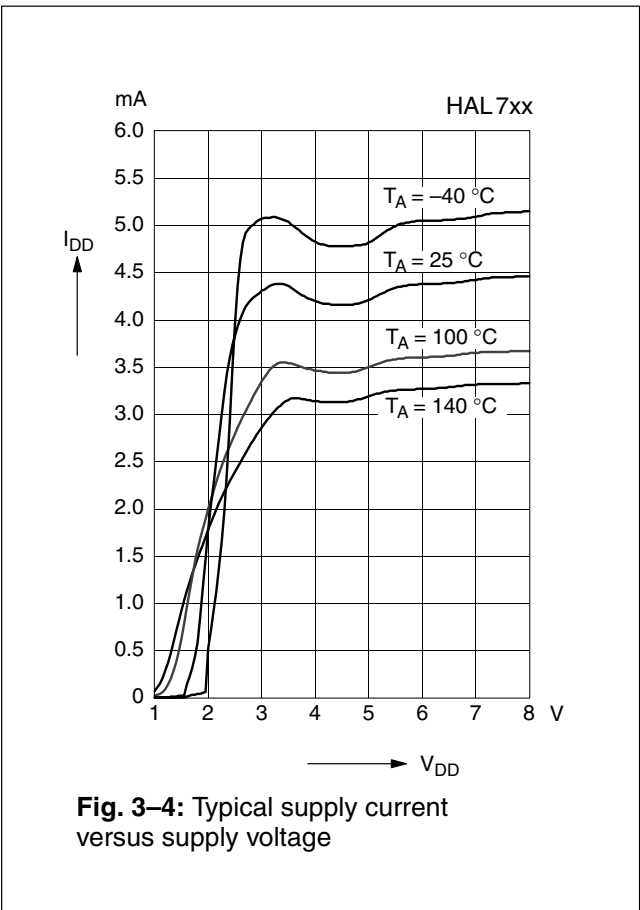
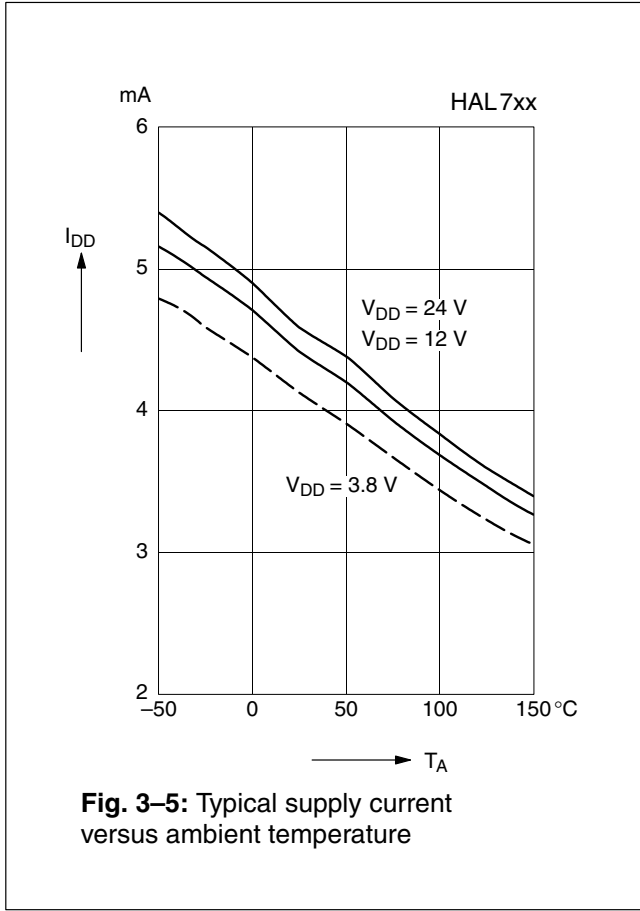
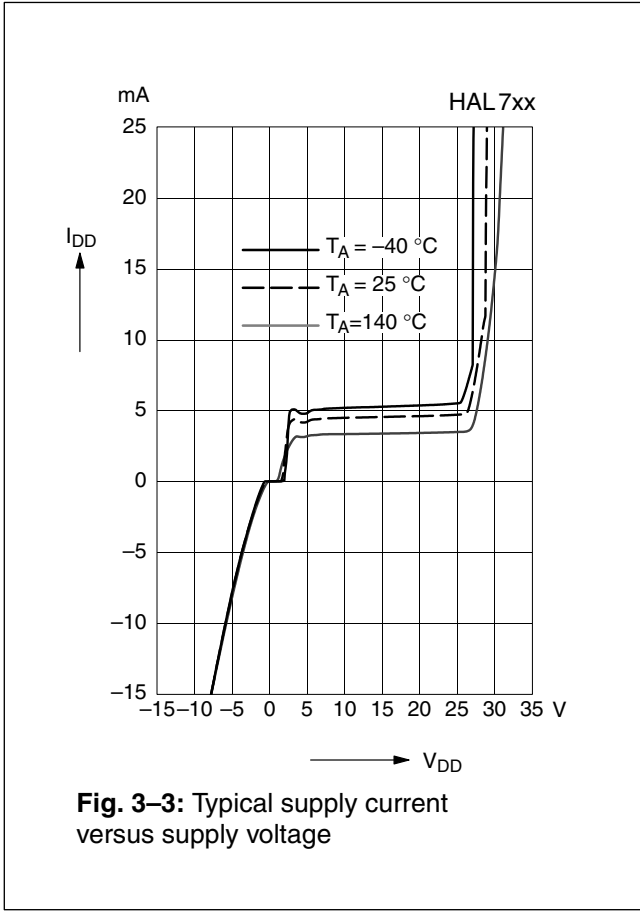
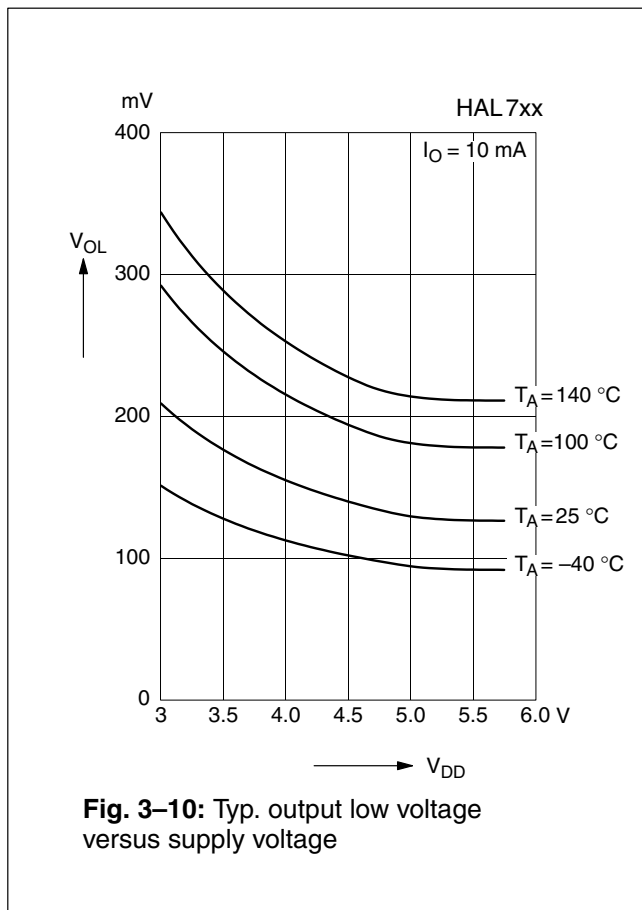
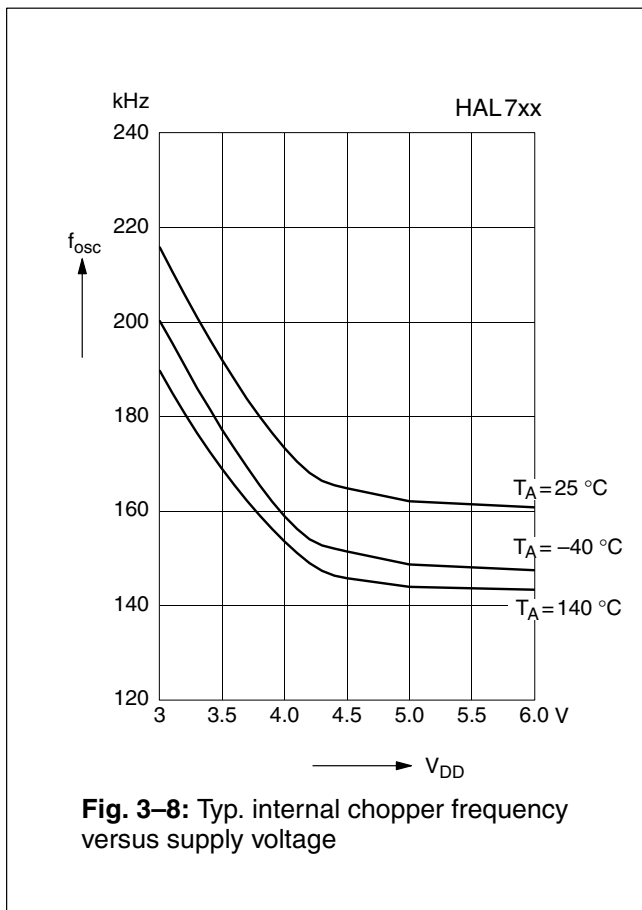
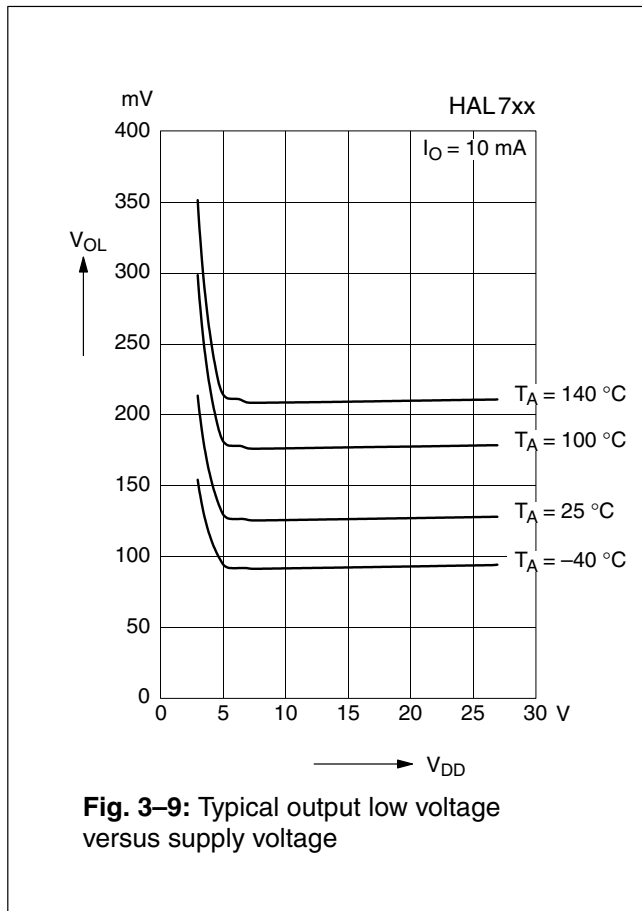
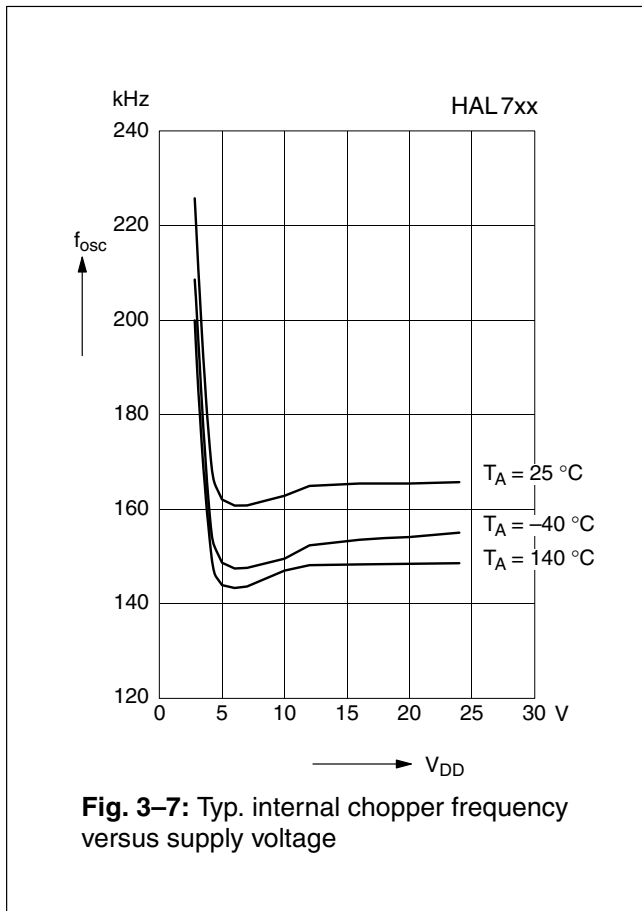


Fig. 3–2: Recommended pad size for SOT-89B
Dimensions in mm





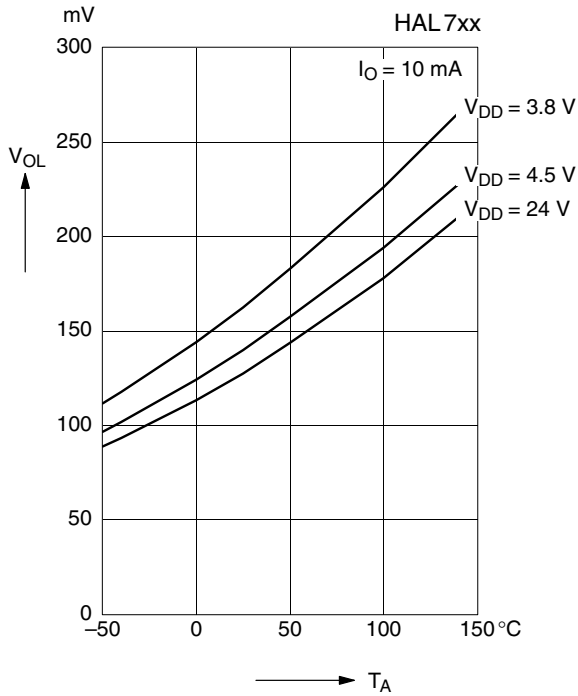


Fig. 3-11: Typical output low voltage versus ambient temperature

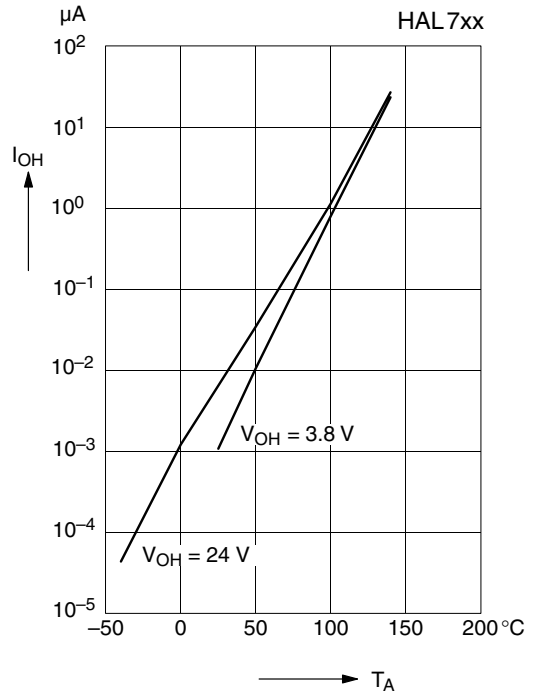


Fig. 3-13: Typical output leakage current versus ambient temperature

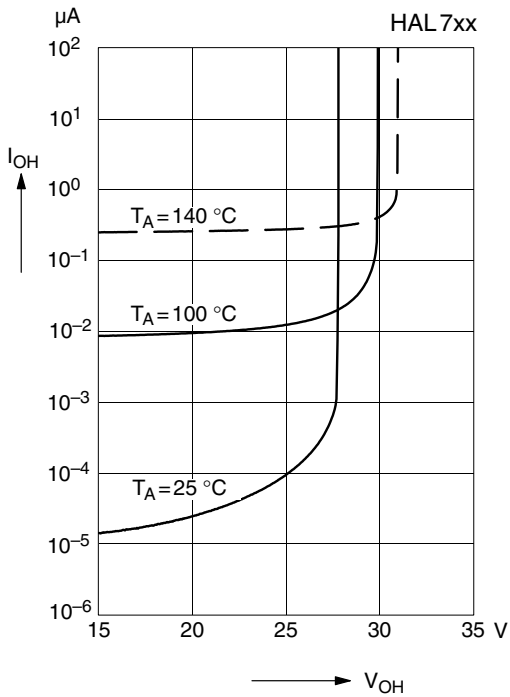


Fig. 3-12: Typical output leakage current versus output voltage

4. Type Description

4.1. HAL700

The HAL700 consists of two independent latched switches (see Fig. 4–1) with closely matched magnetic characteristics controlling two independent open-drain outputs. The Hall plates of the two switches are spaced 2.35 mm apart.

In combination with an active target providing a sequence of alternating magnetic north and south poles, the sensor forms a system generating the signals required to control position, speed, and direction of the target movement.

Magnetic Features

- two independent Hall-switches
- distance of Hall plates: 2.35 mm
- typical B_{ON} : 14.9 mT at room temperature
- typical B_{OFF} : -14.9 mT at room temperature
- temperature coefficient of -2000 ppm/K in all magnetic characteristics
- operation with static magnetic fields and dynamic magnetic fields up to 10 kHz

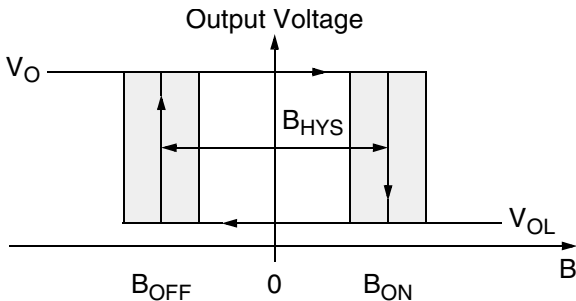


Fig. 4–1: Definition of magnetic switching points for the HAL700

Positive flux density values refer to magnetic south pole at the branded side of the package.

Applications

The HAL700 is the ideal sensors for position-control applications with direction detection and alternating magnetic signals such as:

- multipole magnet applications,
- rotating speed and direction measurement, position tracking (active targets), and
- window lifters.

Magnetic Thresholds

(quasistationary: $dB/dt < 0.5$ mT/ms)

at $T_J = -40$ °C to $+140$ °C, $V_{DD} = 3.8$ V to 24 V, as not otherwise specified

Typical characteristics for $T_J = 25$ °C and $V_{DD} = 5$ V

Parameter	On-Point B_{S1on}, B_{S2on}			Off-Point B_{S1off}, B_{S2off}			Unit
	Min.	Typ.	Max.	Min.	Typ.	Max.	
T_J							
-40 °C	12.5	16.3	20	-20	-16.3	-12.5	mT
25 °C	10.7	14.9	19.1	-19.1	-14.9	-10.7	mT
100 °C	7.7	12.5	17.3	-17.3	-12.5	-7.7	mT
140 °C	6.0	10.9	16.0	-16.0	-10.9	-6.0	mT

Matching B_{S1} and B_{S2}

(quasistationary: $dB/dt < 0.5$ mT/ms)

at $T_J = -40$ °C to $+140$ °C, $V_{DD} = 3.8$ V to 24 V, as not otherwise specified

Typical characteristics for $T_J = 25$ °C and $V_{DD} = 5$ V

Parameter	$B_{S1on} - B_{S2on}$			$B_{S1off} - B_{S2off}$			Unit
	Min.	Typ	Max.	Min.	Typ	Max.	
T_J							
-40 °C	-7.5	0	7.5	-7.5	0	7.5	mT
25 °C	-7.5	0	7.5	-7.5	0	7.5	mT
100 °C	-7.5	0	7.5	-7.5	0	7.5	mT
140 °C	-7.5	0	7.5	-7.5	0	7.5	mT

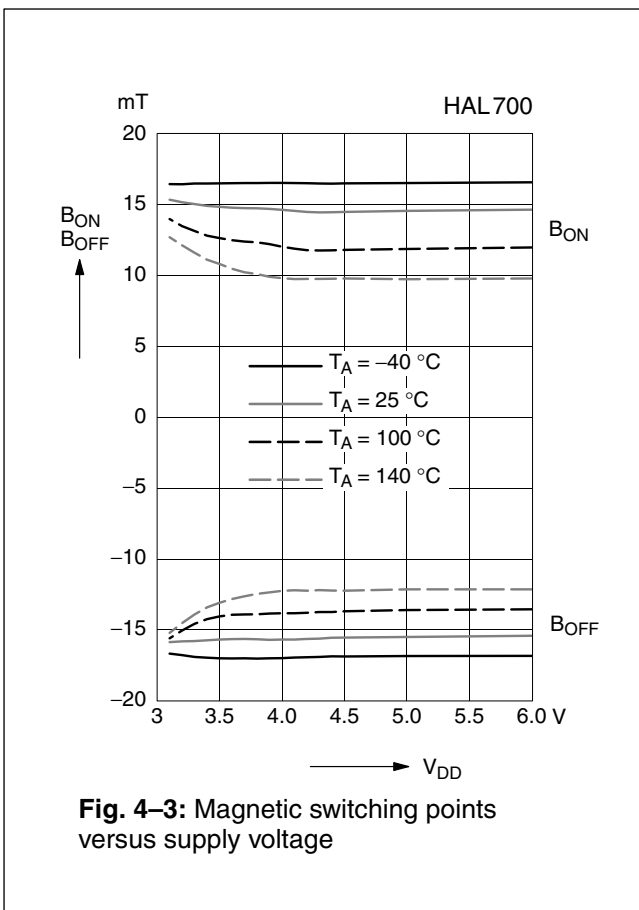
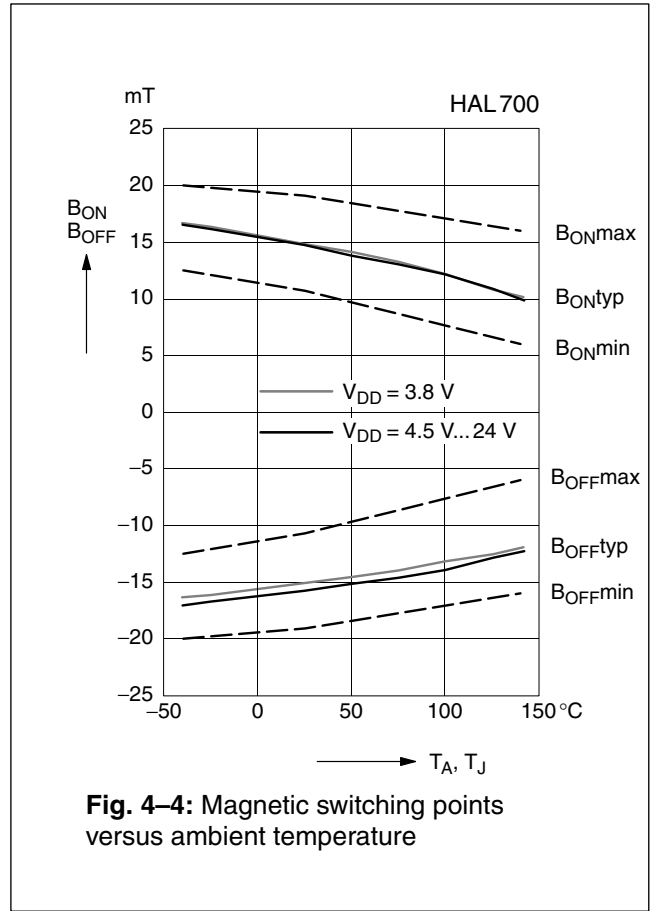
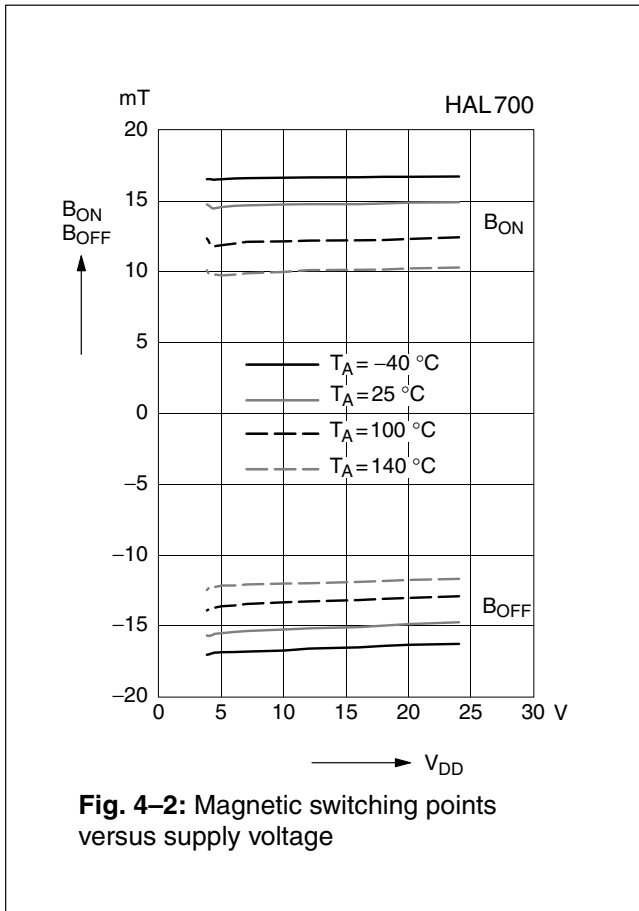
Hysteresis Matching

(quasistationary: $dB/dt < 0.5$ mT/ms)

at $T_J = -40$ °C to $+140$ °C, $V_{DD} = 3.8$ V to 24 V, as not otherwise specified

Typical characteristics for $T_J = 25$ °C and $V_{DD} = 5$ V

Parameter	$(B_{S1on} - B_{S1off}) / (B_{S2on} - B_{S2off})$			Unit
	Min.	Typ.	Max.	
T_J				
-40 °C	0.85	1.0	1.2	–
25 °C	0.85	1.0	1.2	–
100 °C	0.85	1.0	1.2	–
140 °C	0.85	1.0	1.2	–



4.2. HAL740

The HAL740 consists of two independent unipolar switches (see Fig. 4–5) with complementary magnetic characteristics controlling two independent open-drain outputs. The Hall plates of the two switches are spaced 2.35 mm apart.

The S1-Output turns low with the magnetic south pole on the branded side of the package and turns high if the magnetic field is removed. It does not respond to the magnetic north pole on the branded side.

The S2-Output turns low with the magnetic north pole on the branded side of the package and turns high if the magnetic field is removed. It does not respond to the magnetic south pole on the branded side.

Magnetic Features

- two independent Hall-switches
- distance of Hall plates: 2.35 mm
- temperature coefficient of –2000 ppm/K in all magnetic characteristics
- operation with static magnetic fields and dynamic magnetic fields up to 10 kHz

Magnetic Characteristics

(quasistationary: dB/dT < 0.5 T/ms) at T_J = –40 °C to +100 °C, V_{DD} = 3.8 V to 24 V, Typical Characteristics for V_{DD} = 12 V. Absolute values common to both Hall switches. The Hall switches S1 and S2 only differ in sign. For S1 the sign is positive, for S2 negative. Positive flux density values refer to the magnetic south pole at the branded side of the package.

Parameter	On point B _{ON}			Off point B _{OFF}			Hysteresis B _{HYS}			Magnetic Offset			Unit
	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
T _J –40 °C	8.5	12.3	16.0	5.0	8.8	12.5	2.0	–	5.5	–	10.6	–	mT
25 °C	7.0	11.5	16.0	3.5	8.0	12.5	2.0	–	6.0	–	9.8	–	mT
100 °C	5.5	10.8	16.0	2.0	7.0	12.5	1.5	–	6.5	–	8.9	–	mT
140 °C	4.6	10.4	16.0	1.1	6.8	12.5	1.0	–	7.0	–	8.6	–	mT

The hysteresis is the difference between the switching points $B_{HYS} = B_{ON} - B_{OFF}$
 The magnetic offset is the mean value of the switching points $B_{OFFSET} = (B_{ON} + B_{OFF}) / 2$

Applications

The HAL740 is the ideal sensor for applications which require both magnetic polarities, such as:

- position and direction detection, or
- position and end point detection with either magnetic pole (omnipolar switch).

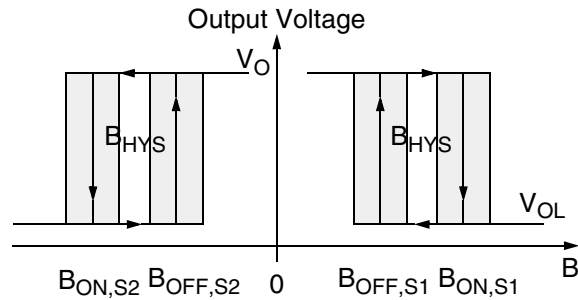
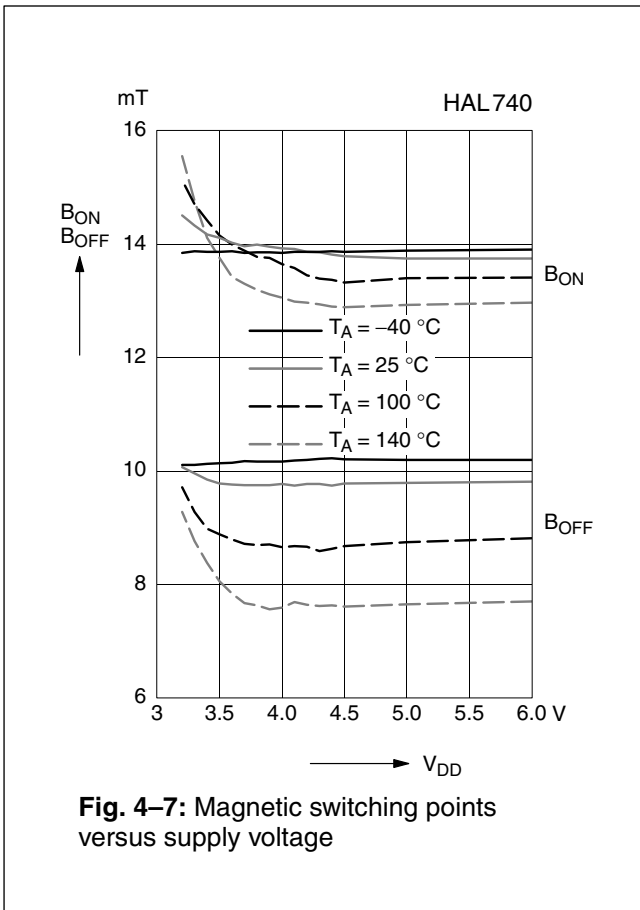
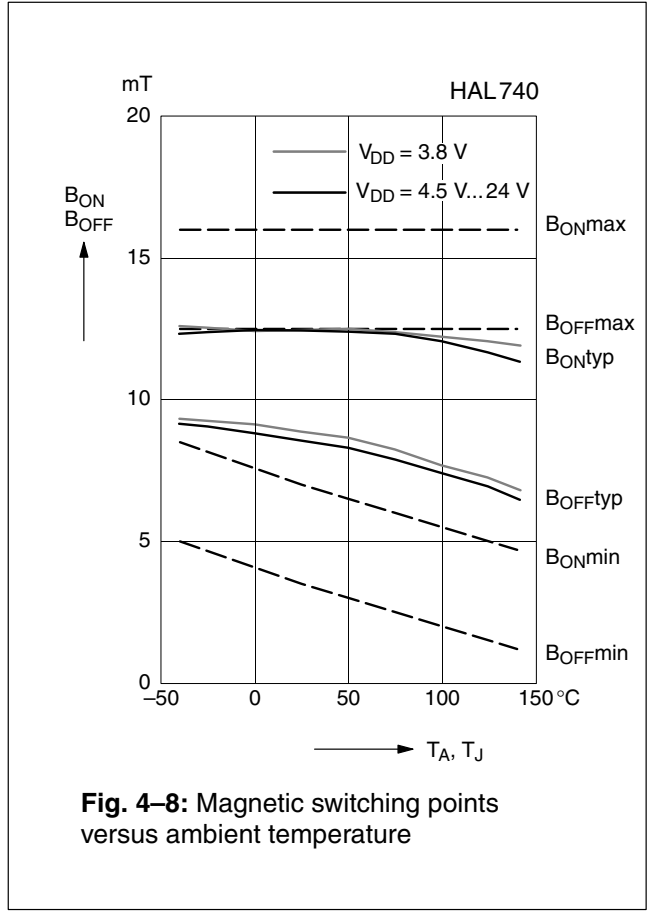
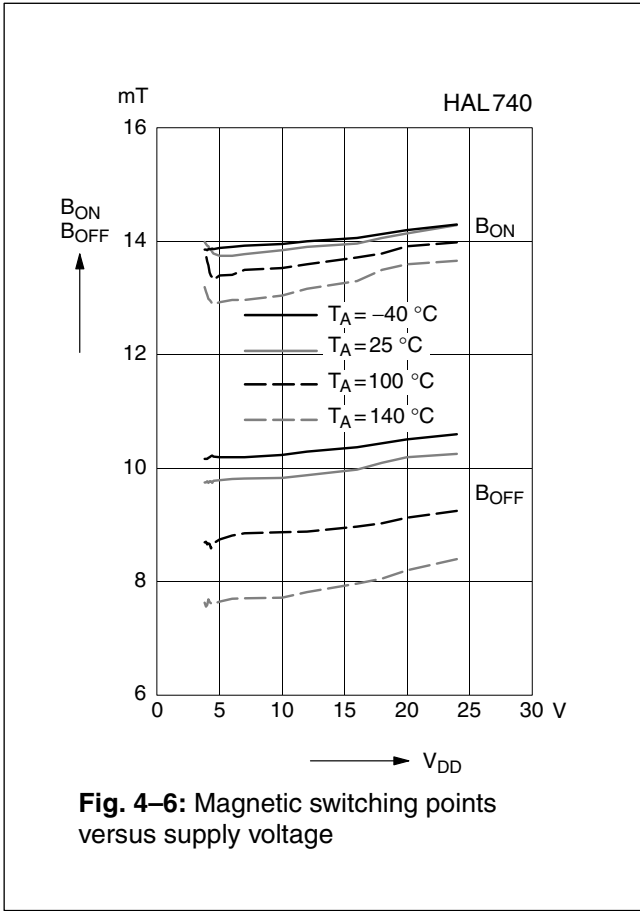


Fig. 4–5: Definition of magnetic switching points for the HAL740



5. Application

5.1. Ambient Temperature

Due to the internal power dissipation, the temperature on the silicon chip (junction temperature T_J) is higher than the temperature outside the package (ambient temperature T_A).

$$T_J = T_A + \Delta T$$

At static conditions, the following equation is valid:

$$\Delta T = I_{DD} * V_{DD} * R_{th}$$

For typical values, use the typical parameters. For worst case calculation, use the max. parameters for I_{DD} and R_{th} , and the max. value for V_{DD} from the application.

For all sensors, the junction temperature range T_J is specified. The maximum ambient temperature T_{Amax} can be calculated as:

$$T_{Amax} = T_{Jmax} - \Delta T$$

5.2. Extended Operating Conditions

All sensors fulfil the electrical and magnetic characteristics when operated within the “Recommended Operating Conditions” (see Section 3.5. on page 9).

Supply Voltage Below 3.8 V

Typically, the sensors operate with supply voltages above 3 V, however, below 3.8 V some characteristics may be outside the specification.

Note: The functionality of the sensor below 3.8 V is not tested. For special test conditions, please contact Micronas.

5.3. Start-up Behavior

Due to the active offset compensation, the sensors have an initialization time (enable time $t_{en(O)}$) after applying the supply voltage. The parameter $t_{en(O)}$ is specified in the “Electrical Characteristics” (see Section 3.6. on page 10).

During the initialization time, the output states are not defined and the outputs can toggle. After $t_{en(O)}$, both outputs will be either high or low for a stable magnetic field (no toggling). The outputs will be low if the applied magnetic flux density B exceeds B_{ON} and high if B drops below B_{OFF} .

For magnetic fields between B_{OFF} and B_{ON} , the output states of the Hall sensor after applying V_{DD} will be either low or high. In order to achieve a well-defined output state, the applied magnetic flux density must be above B_{ONmax} , respectively, below B_{OFFmin} .

5.4. EMC and ESD

For applications that cause disturbances on the supply line or radiated disturbances, a series resistor and a capacitor are recommended (see Fig. 5–1). The series resistor and the capacitor should be placed as closely as possible to the Hall sensor.

Please contact Micronas for detailed investigation reports with EMC and ESD results.

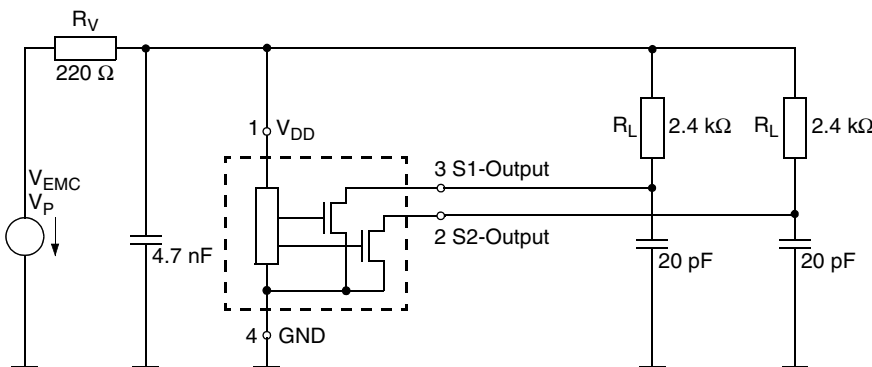


Fig. 5–1: Test circuit for EMC investigations

6. Data Sheet History

1. Data Sheet: "HAL 700, HAL 740 Dual Hall-Effect Sensors with Independent Outputs", June 13, 2002, 6251-477-1DS. First release of the data sheet.

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